

-55V Single P-Channel HEXFET Power MOSFET in a TO-220AB package; Similar to the IRF9Z34N with Lead-Free Packaging.

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-220AB
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRF9Z34NPBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

Advanced Process Technology
 Surface Mount (IRF9Z34NS)
 Low-profile through-hole (IRF9Z34NL)
 175°C Operating Temperature
 Fast Switching
 P-Channel
 Fully Avalanche Rated

Features

RoHS Compliant

Low RDS(on)

Industry-leading quality

Dynamic dv/dt Rating

Fast Switching

Fully Avalanche Rated

175°C Operating Temperature

P-Channel MOSFET



Related Products



[IRLTS6342TRPBF](#)

Infineon Technologies Corporation
TSOP-6



[IRF9310PBF](#)

Infineon Technologies Corporation
SOIC-8



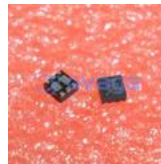
[IRF9358TRPBF](#)

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[IRFB3307ZPBF](#)

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TO-220AB



[IRLHS6376TRPBF](#)

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PQFN2x2DD



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